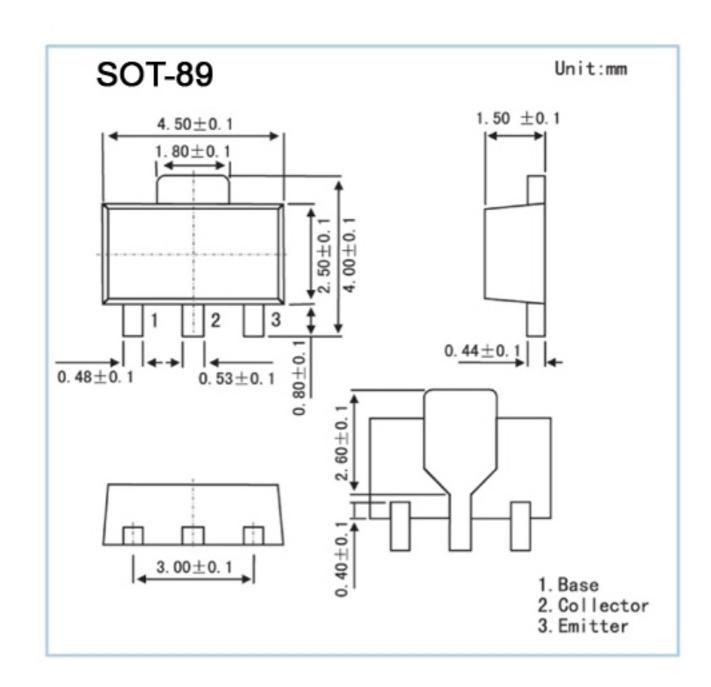


Low Frequency Transistor

Features

- Low VCE(sat).VCE(sat) = -0.35V (Typ.)(Ic/IB = -4A / -0.1A)
- Excellent DC current gain
- Epitaxial planar type
- PNP silicon transistor



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	Vсво	-30	V
Collector-emitter voltage	VCEO	-20	V
Emitter-base voltage	Vево	-6	V
Collector current	Ic	-5	Α
Collector current(Pulse)	ICP *	-10	Α
Collector power dissipation	Pc	0.5	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

^{*} Single pulse, Pw=10ms

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
Collector-base breakdown voltage	ВУсво	Ic=-50μA	-30			٧
Collector-emitter breakdown voltage	BVceo	Ic=-1mA	-20			٧
Emitter-base breakdown voltage	ВУЕВО	IE=-50μA	-6			V
Collector cutoff current	Ісво	Vcb=-20V			-0.5	μΑ
Emitter cutoff current	ІЕВО	VEB=-5V			-0.5	μΑ
DC current transfer ratio	VCE(sat)	Ic=-4A,I _B =-0.1A			-1	٧
Collector-emitter saturation voltage	hFE	Vce=-2V, Ic=-0.5A	82		390	
Transition frequency	Cob	Vce=-6V, Ie=50mA, f=30MHz		120		MHz
Output capacitance	f⊤	Vcb=-20V, IE=0A, f=1MHz		60		pF

hfe Classification

Marking	BH			
Rank	Р	Q	R	
hFE	82~180	120~270	180~390	

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Shikues manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B